

BYC15X-600

Rectifier diode, hyperfast Rev. 01 — 29 November 2007

Product data sheet

Product profile

1.1 General description

Hyperfast, epitaxial rectifier diode in a SOD113 (2-lead TO-220F) plastic package.

1.2 Features

- Extremely fast switching
- Low reverse recovery current
- Reduces switching loss in associated **MOSFET**
- Low thermal resistance
- Isolated package

1.3 Applications

- Half-bridge or full-bridge switched-mode Continuous Current Mode (CCM) Power power supplies
- Half-bridge lighting ballasts
- Factor Correction (PFC)

1.4 Quick reference data

- $V_{RRM} \le 600 \text{ V}$
- $V_F = 1.32 \text{ V (typ)}$

- $I_{F(AV)} \le 15 A$
- $t_{rr} = 19 \text{ ns (typ)}$

Pinning information

Table 1. **Pinning**

Pin	Description	Simplified outline	Symbol
1	cathode (k)		
2	anode (a)	mb	k ——— a 001aaa020
mb	mounting base; isolated		
		SOD113 (2-lead TO-22	0F)



3. Ordering information

Table 2. Ordering information

Type number	Package					
	Name	Description	Version			
BYC15X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'	SOD113			

4. Limiting values

Table 3. Limiting values

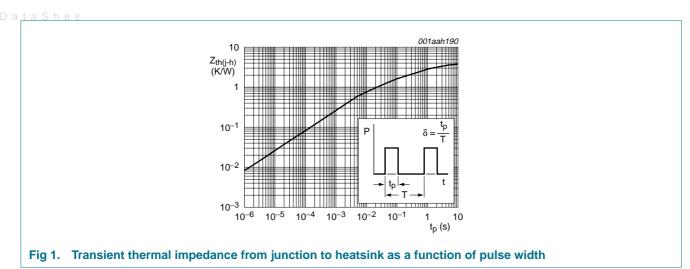
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	square waveform; δ = 1.0; $T_h \le 100~^{\circ}C$	-	500	V
I _{F(AV)}	average forward current	square waveform; δ = 0.5; $T_h \leq$ 25 $^{\circ}C$	-	15	А
I _{FRM}	repetitive peak forward current	square waveform; δ = 0.5; $T_h \leq$ 25 °C; t_p = 25 μs	-	30	Α
I _{FSM}	non-repetitive peak forward	t = 10 ms; sinusoidal waveform	-	200	Α
•	current	t = 8.3 ms; sinusoidal waveform	-	220	Α
T _{stg}	storage temperature		-40	+150	°C
Tj	junction temperature		-	150	°C

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; see Figure 1	-	-	3.6	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	55	-	K/W



6. Isolation characteristics

Table 5. Isolation limiting values and characteristics

 $T_h = 25 \,^{\circ}C$ unless otherwise specified.

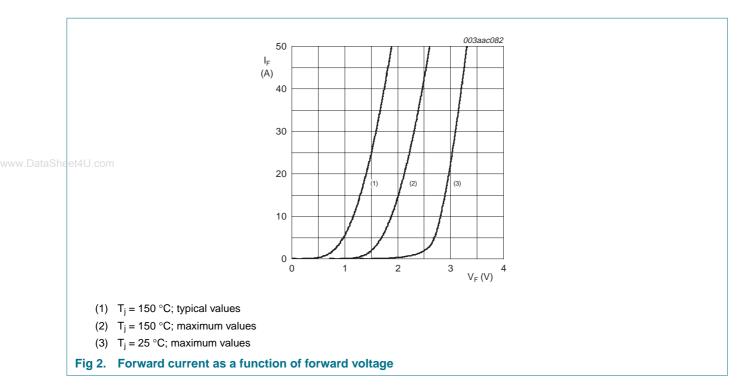
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; f = 50 Hz to 60 Hz; sinusoidal waveform; relative humidity $\leq 65 \%$; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from pin 1 (cathode) to external heatsink; f = 1 MHz	-	10	-	pF

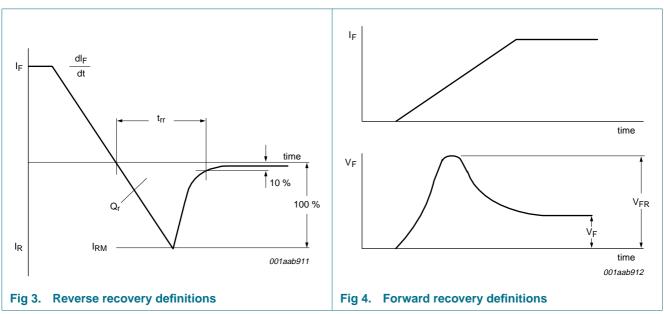
7. Characteristics

Table 6. Characteristics

 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _F	forward voltage	$I_F = 15 \text{ A}; T_j = 150 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 2}}{}$	-	1.32	2.03	V
		$I_F = 30 \text{ A}$; $T_j = 150 ^{\circ}\text{C}$; see Figure 2	-	1.64	2.34	V
		I _F = 15 A; see <u>Figure 2</u>	-	1.89	2.9	V
I _R	reverse current	V _R = 600 V	-	12	200	μΑ
		$V_R = 500 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	1.1	3.0	mA
Dynamic c	characteristics					
t _{rr}	reverse recovery time	I_F = 1 A to V_R = 30 V; dI_F/dt = 50 A/ μ s; see Figure 3	-	35	55	ns
		I_F = 15 A to V_R = 400 V; dI_F/dt = 500 A/ μ s; see Figure 3				
		T _j = 25 °C	-	19	-	ns
		T _j = 100 °C	-	32	40	ns
I _{RM}	peak reverse recovery current	I_F = 15 A to V_R = 400 V; T_j = 125 °C; see Figure 3				
		$dI_F/dt = 50 A/\mu s$	-	3.0	7.5	Α
		$dI_F/dt = 500 A/\mu s$	-	9.5	12	Α
V_{FR}	forward recovery voltage	$I_F = 15 \text{ A}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; see Figure 4	-	8	11	V





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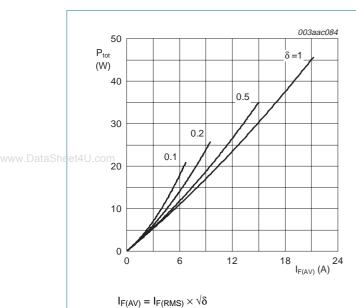
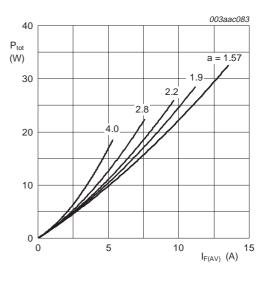


Fig 5. Forward power dissipation as a function of average forward current; square waveform; maximum values



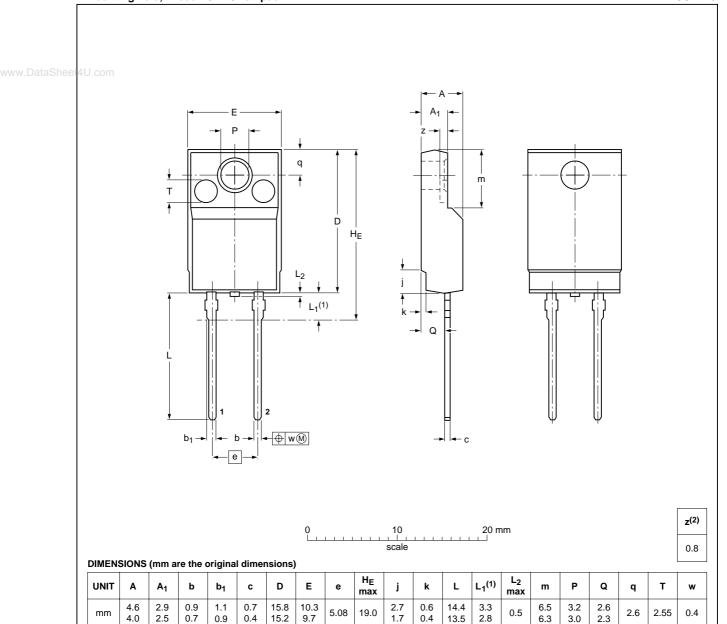
 $a = form factor = I_{F(RMS)} / I_{F(AV)}$

Fig 6. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

8. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'

SOD113



Notes

1. Terminals are uncontrolled within zone L₁.

2. z is depth of T.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOD113		2-lead TO-220F			02-04-09 07-06-18	

Fig 7. Package outline SOD113 (2-lead TO-220F)



9. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYC15X-600_1	20071129	Product data sheet	-	-

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10. Legal information

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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